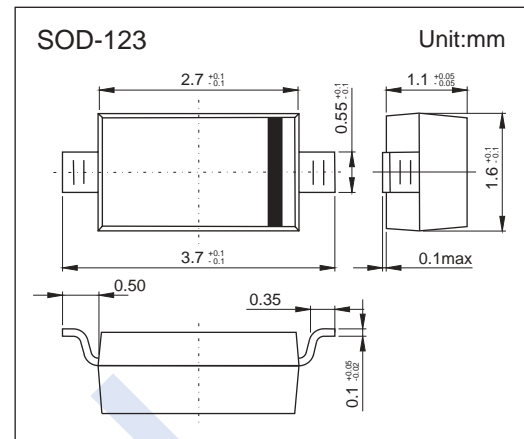


Switching Diodes

1KS3011E,1KS3013E,1KS3014E

■ Features

- Silicon Epitaxial Planar Diodes
- For General Purpose
- This diode is also available in other case.
- Small Signal Diodes



■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	1KS3013E	1KS3014E	1KS3011E	Unit
Repetitive Peak Reverse Voltage	V_{RRM}	120	200	250	V
Continuous Reverse Voltage	V_R	100	150	200	
Forward DC Current	I_F	250			mA
Averaged Forward Current	I_{FAV}	200			
Repetitive Peak Forward Current @ $f > 50\text{Hz}$,	I_{FRM}	625			
Surge Forward Current @ $t < 1\text{s}$	I_{FSM}	1			A
Power Dissipation	P_D	410			mW
Thermal Resistance Junction to Ambient	R_{thJA}	375			$^\circ\text{C/W}$
Junction Temperature	T_j	150			$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 to 150			

Switching Diodes

1KS3011E, 1KS3013E, 1KS3014E

Electrical Characteristics $T_a = 25^\circ\text{C}$

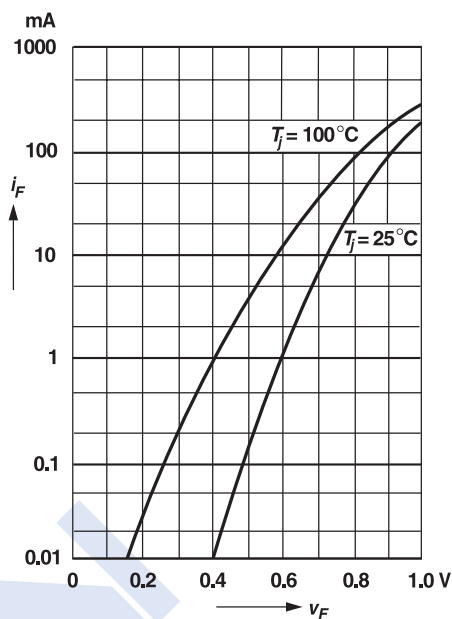
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Reverse breakdown voltage	1KS3013E	$I_R = 1\text{mA}$	120			V
	1KS3014E		200			
	1KS3011E		250			
Forward voltage	V_F	$I_F = 100\text{mA}$			1	
		$I_F = 200\text{mA}$			1.25	
Reverse voltage leakage current	1KS3013E	$V_R = 100\text{V}$			100	nA
	1KS3013E	$V_R = 100\text{V}, T_J = 100^\circ\text{C}$			15	μA
	1KS3014E	$V_R = 150\text{V}$			100	nA
	1KS3014E	$V_R = 150\text{V}, T_J = 100^\circ\text{C}$			15	μA
	1KS3011E	$V_R = 200\text{V}$			100	nA
	1KS3011E	$V_R = 200\text{V}, T_J = 100^\circ\text{C}$			15	μA
Dynamic Forward Resistance	r_f	$I_F = 10\text{mA}$		5		Ω
Reverse Recovery Time	t_{rr}	$I_F = I_R = 30\text{mA}, I_{rr} = 3\text{mA}, R_L = 100\text{m}\Omega$			50	ns
Diode capacitance	C_D	$V_R = 0\text{V}, f = 1\text{MHz}$		1.5		pF

Marking

NO.	1KS3013E	1KS3014E	1KS3011E
Marking	A8	T2	S2E

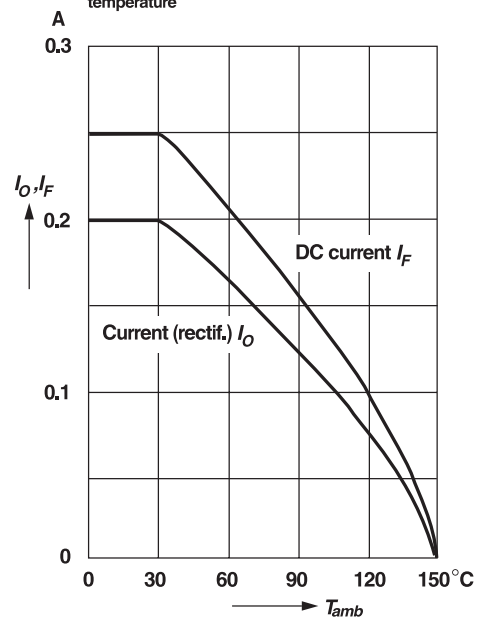
Typical Characteristics

Forward characteristics



Admissible forward current versus ambient temperature

Valid provided that electrodes are kept at ambient temperature



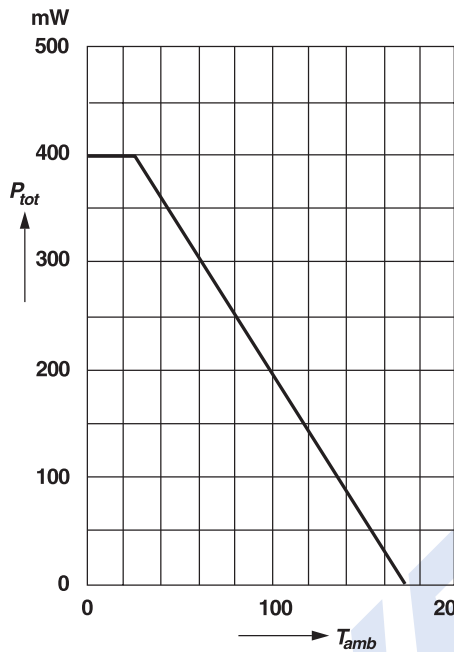
Switching Diodes

1KS3011E, 1KS3013E, 1KS3014E

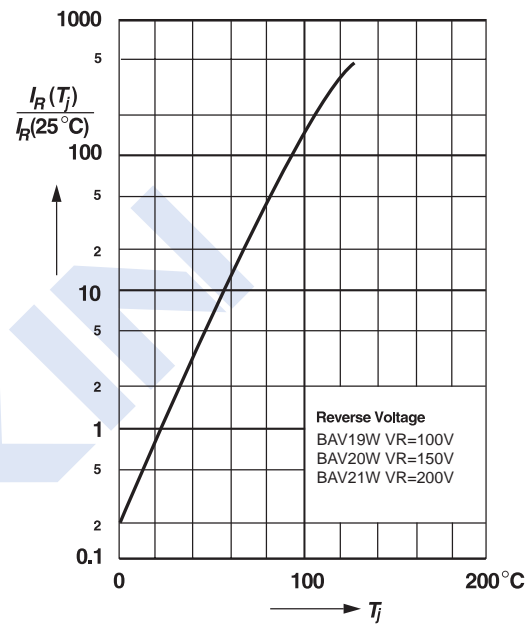
■ Typical Characteristics

Admissible power dissipation versus ambient temperature

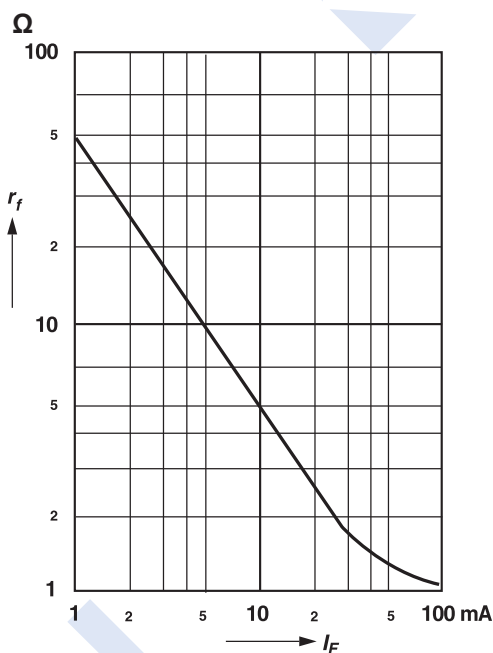
Valid provided that electrodes are kept at ambient temperature



Leakage current versus junction temperature



Dynamic forward resistance versus forward current



Capacitance versus reverse voltage

